

Docket No.: 60188-589

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of

Kaoru INOUE, et al.

Serial No.: 10/620,430

Filed: July 17, 2003



: Customer Number: 20277

: Confirmation Number: 1098

: Group Art Unit:

: Examiner: Unknown

For: METHOD FOR FABRICATING SEMICONDUCTOR DEVICE

INFORMATION DISCLOSURE STATEMENT

Mail Stop IDS
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Dear Sir:

In accordance with the provisions of 37 C.F.R. 1.56, 1.97 and 1.98, the attention of the Patent and Trademark Office is hereby directed to the documents listed on the attached form PTO-1449. It is respectfully requested that the documents be expressly considered during the prosecution of this application, and that the documents be made of record therein and appear among the "References Cited" on any patent to issue therefrom.

This Information Disclosure Statement is being filed within three months of the U.S. filing date OR before the mailing date of a first Office Action on the merits. No certification or fee is required.

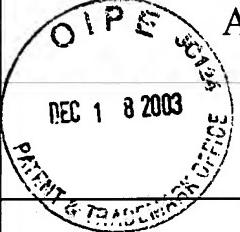
Please charge any shortage in fees due in connection with the filing of this paper, including extension of time fees, to Deposit Account 500417 and please credit any excess fees to such deposit account.

Respectfully submitted,

MCDERMOTT, WILL & EMERY

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INFORMATION DISCLOSURE CITATION IN AN APPLICATION  (PTO-1449)			ATTY. DOCKET NO. 60188-589	SERIAL NO. 10/620,430			
			APPLICANT Kaoru INOUE, et al.				
			FILING DATE July 17, 2003	GROUP			
U.S. PATENT DOCUMENTS							
EXAMINER'S INITIALS	CITE NO.	Document Number Number-Kind Code ₂ (<i>if known</i>)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear		
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FOREIGN PATENT DOCUMENTS					Translation		
EXAMINER'S INITIALS	CITE NO.	Foreign Patent Document Country Codes-Number & Kind Codes (<i>if known</i>)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines Where Relevant Figures Appear	Yes	No
OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)							
EXAMINER'S INITIALS	CITE NO.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.					
		C.F. Lin et al., "Improved Contact Performance of GaN Film Using Si Diffusion", 2000 American Institute of Physics, Applied Physics Letters, Vo. 76, No. 14, pp. 1878-1880, April 3, 2000					
		Hiroyuki MASATO et al., "Novel High Drain Breakdown Voltage AlGaN/GaN HFETs Using Selective Thermal Oxidation Process", IEEE, IEDM 16.2.1-16.2.4, pp. 377-380, 2000					
EXAMINER			DATE CONSIDERED				

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

1 Applicant's unique citation designation number (optional). 2 Applicant is to place a check mark here if English language Translation is attached.